

**Silicon NPN Power Transistors**

**2SC1456**

**DESCRIPTION**

- With TO-66 package
- High collector-emitter voltage  
:  $V_{CEO}=300V$

**APPLICATIONS**

- For use in line-operated color TV chroma output circuits and sound output circuits.

**PINNING**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

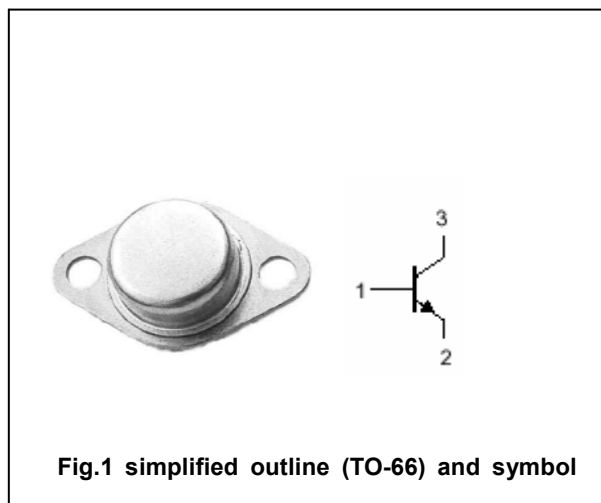


Fig.1 simplified outline (TO-66) and symbol

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		0.15	A
$P_T$	Collector power dissipation	$T_C=25^\circ C$	10	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =10μA ; I <sub>E</sub> =0	300			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA ; I <sub>B</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10μA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =5mA			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V ; I <sub>E</sub> =0			1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =4V ; I <sub>C</sub> =0			1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =50mA ; V <sub>CE</sub> =10V	30		150	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =10mA ; V <sub>CE</sub> =30V	55			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions